

N-Channel Enhancement Mode Field Effect Transistor with Schottky Diode

General Description

The VBA1310S uses advanced trench technology to provide excellent $R_{DS(ON)}$, shoot-through immunity and body diode characteristics. This device is suitable for use as a synchronous switch in PWM applications. The co-packaged Schottky Diode boosts efficiency further.

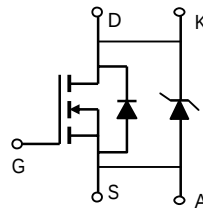
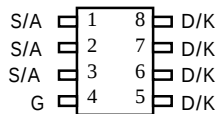
Features

V_{DS} (V) = 30V
 I_D = 12 A (V_{GS} = 10V)
 $R_{DS(ON)}$ < 11.5m Ω (V_{GS} = 10V)
 $R_{DS(ON)}$ < 13m Ω (V_{GS} = 4.5V)

SCHOTTKY

V_{DS} (V) = 30V, I_F = 3A, V_F < 0.5V@1A

SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 12		V
Continuous Drain Current ^A	I_D	12		A
		10.4		
Pulsed Drain Current ^B	I_{DM}	40		
Schottky reverse voltage	V_{KA}		30	V
Continuous Forward Current ^A	I_F		4.4	A
			3.2	
Pulsed Diode Forward Current ^B	I_{FM}		30	
Power Dissipation	P_D	3.1	3.1	W
		2	2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	28	40	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		54	75	°C/W
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	21	30	°C/W

Thermal Characteristics: Schottky					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	36	40	°C/W
Maximum Junction-to-Ambient ^A	Steady-State		67	75	°C/W
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	25	30	°C/W

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}C$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10s$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}C$. The SOA curve provides a single pulse rating.

F: The Schottky appears in parallel with the MOSFET body diode, even though it is a separate chip. Therefore, we provide the net forward drop, capacitance and recovery characteristics of the MOSFET and Schottky. However, the thermal resistance is specified for each chip separately.

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current. (Set by Schottky leakage)	$V_R=30\text{V}$		0.007		mA
		$V_R=30\text{V}$, $T_J=125^{\circ}\text{C}$		3.2		
		$V_R=30\text{V}$, $T_J=150^{\circ}\text{C}$		12		
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	0.5		2.0	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=13\text{A}$		8.0		m Ω
		$T_J=125^{\circ}\text{C}$		11.0		
		$V_{GS}=4.5\text{V}$, $I_D=12.2\text{A}$		9.0		m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=13\text{A}$	30	37		S
V_{SD}	Diode + Schottky Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.45	0.5	V
I_S	Maximum Body-Diode + Schottky Continuous Current				5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		3656		pF
C_{oss}	Output Capacitance (FET+Schottky)			322		pF
C_{rss}	Reverse Transfer Capacitance			168		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		0.86	1.1	Ω
SWITCHING PARAMETERS						
$Q_g(4.5\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=13\text{A}$		30.5	36	nC
Q_{gs}	Gate Source Charge			4.6		nC
Q_{gd}	Gate Drain Charge			8.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1.1\Omega$, $R_{GEN}=0\Omega$		6.2	9	ns
t_r	Turn-On Rise Time			4.8	7	ns
$t_{D(off)}$	Turn-Off DelayTime			55	75	ns
t_f	Turn-Off Fall Time			7.3	11	ns
t_{rr}	Body Diode+Schottky Reverse Recovery Time	$I_F=13\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		20.3	25	ns
Q_{rr}	Body Diode+Schottky Reverse Recovery Charge	$I_F=13\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		8.4	12.5	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

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Rev5: August 2005.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

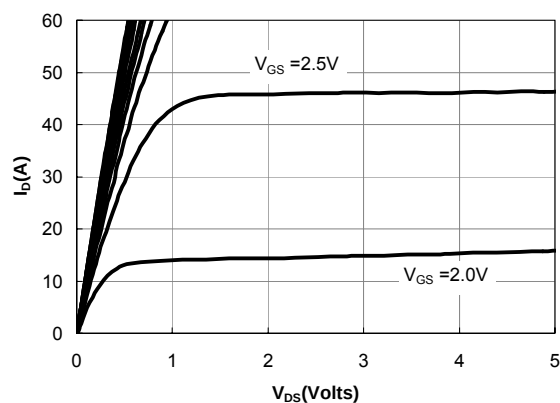


Figure 1: On-Regions Characteristics

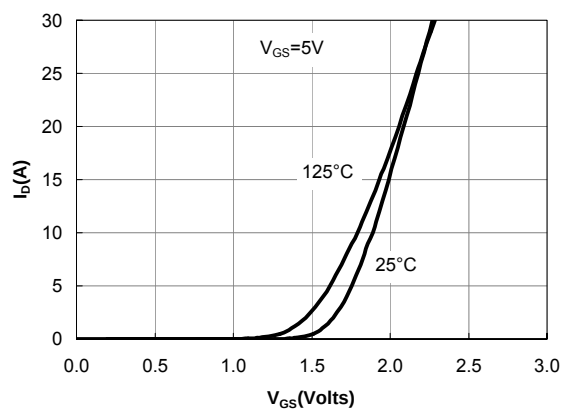


Figure 2: Transfer Characteristics

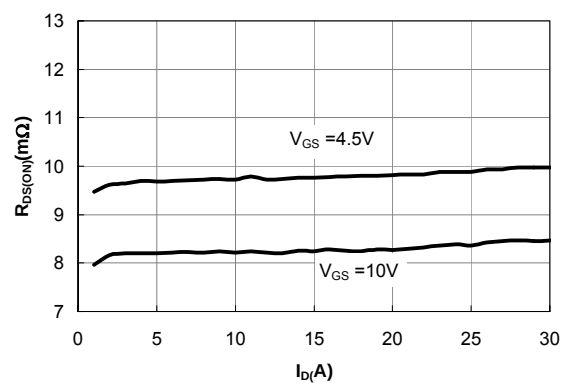


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

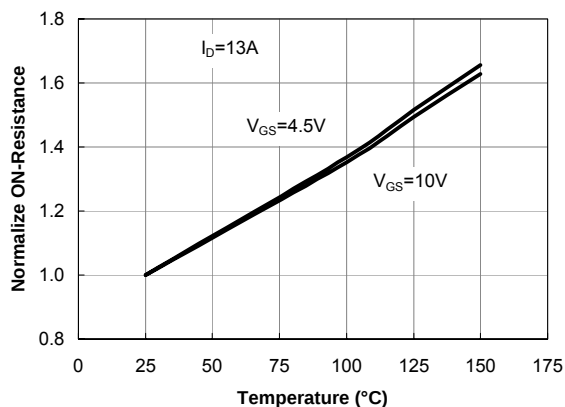


Figure 4: On-Resistance vs. Junction Temperature

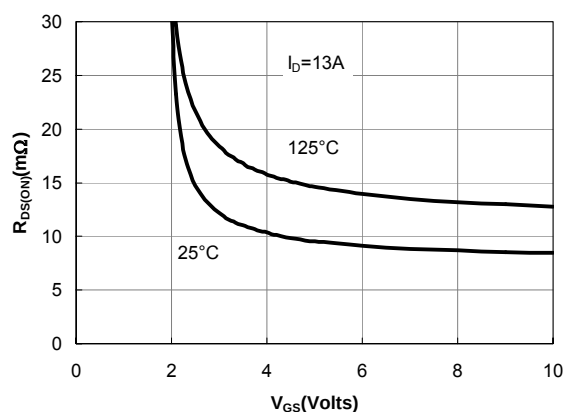
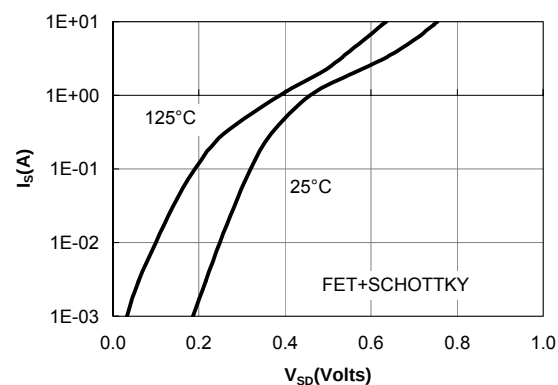
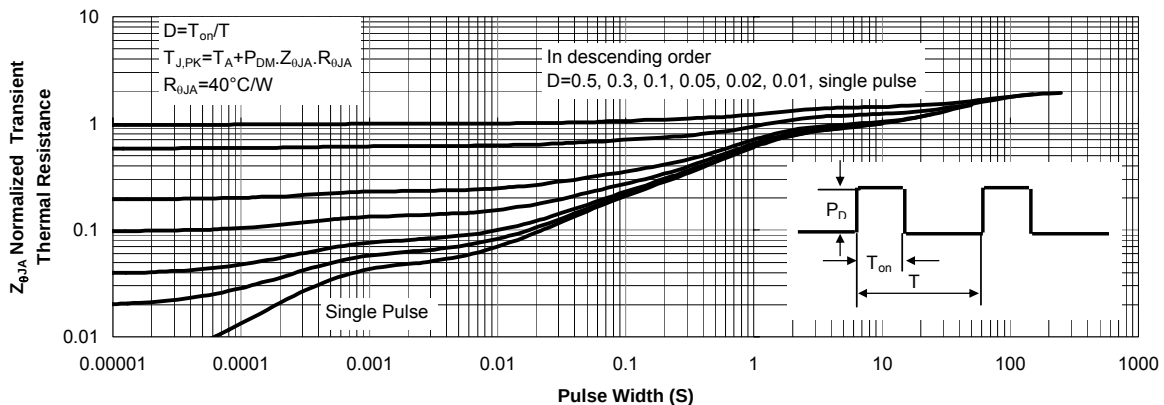
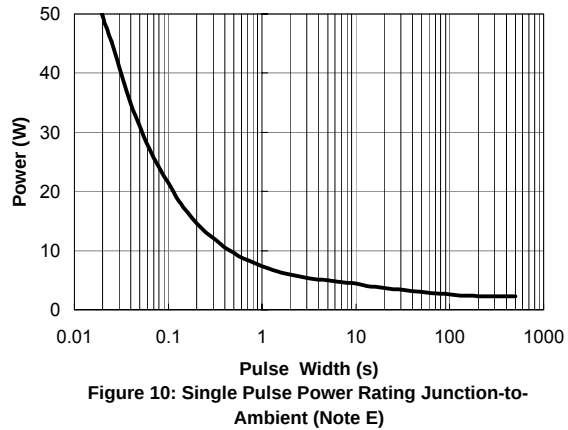
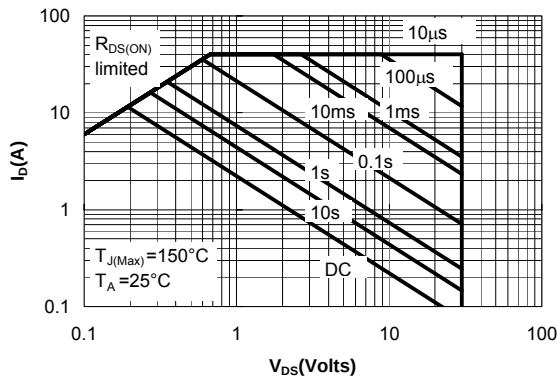
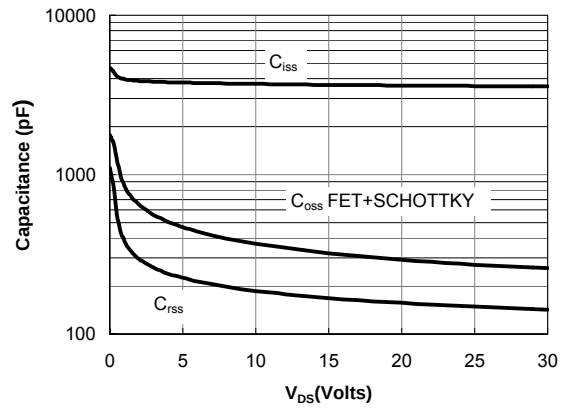
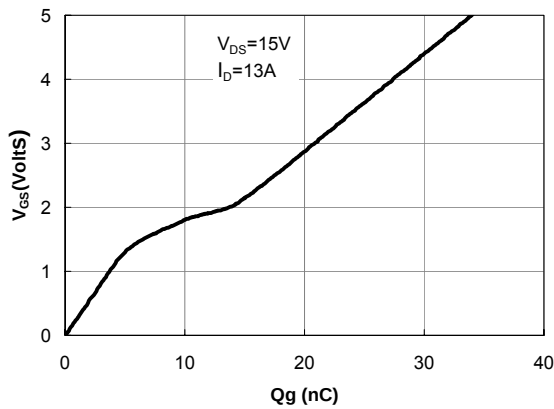


Figure 5: On-Resistance vs. Gate-Source Voltage

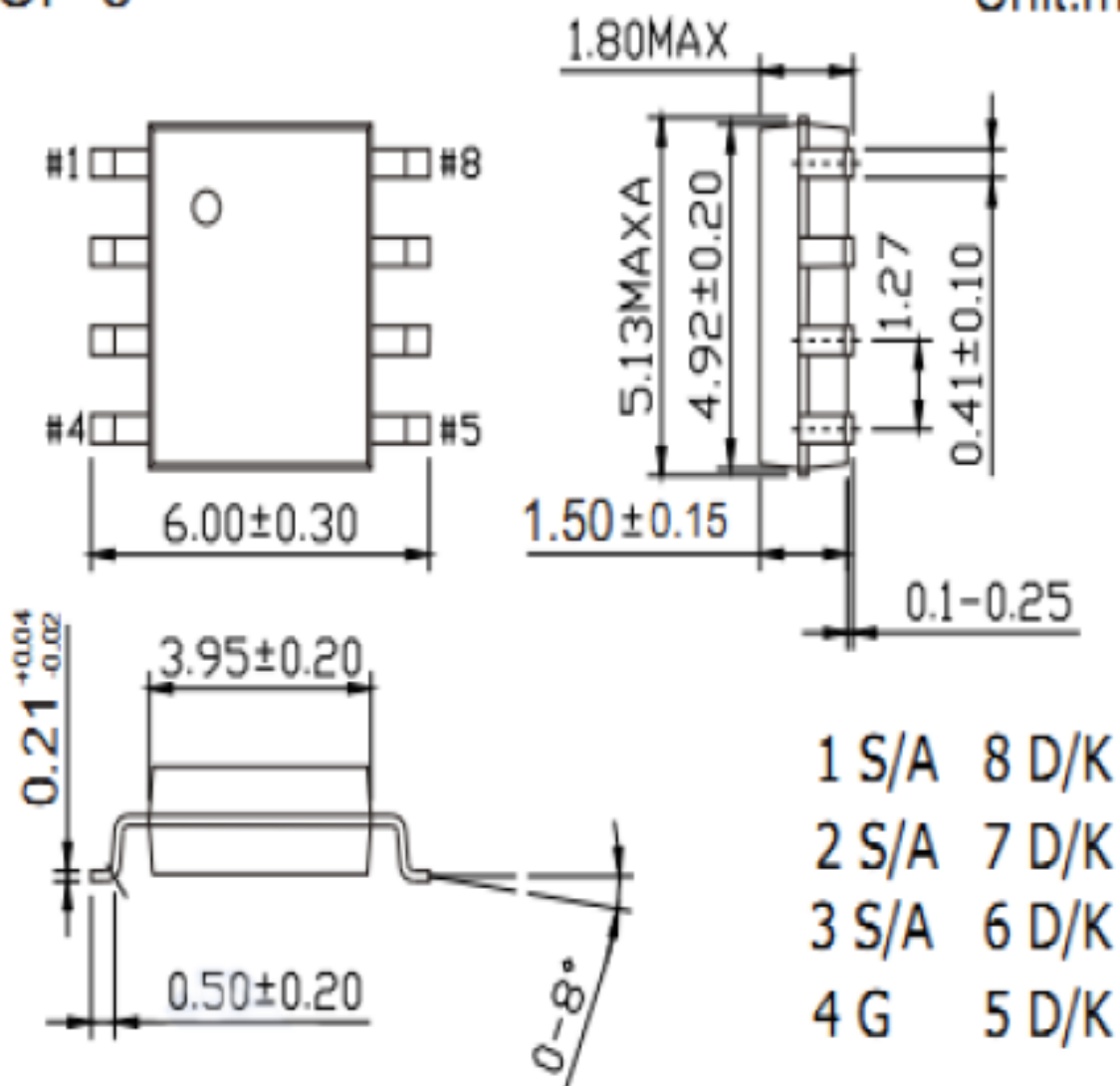
Figure 6: Body-Diode Characteristics
(Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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Unit:mm



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